

# **Thin-SOI Solutions**

### **Applications**

Our customised Thin-SOI solutions are suitable for the following fields:

- **RF** Filters
- Optoelectronics .
- Image Sensing •
- Wireless Connectivity
- Flexible-Hybrid Electronics
- **RF MEMS**

#### End Markets:

Telecommunications

↓ 0.244um

SEL

- Consumer
- Power
- Medical



With the wide range of specifications for both silicon wafers and the thermally grown Buried Oxide Layer, the IceMOS Thin-SOI wafer range covers applications such as Silicon Photonics to SAW filters.

By making continuous improvements to our processes in a Lean Six Sigma environment, IceMOS Technology offer world class product quality, competitive cost structure plus rapid turnaround makes IceMOS Technology your ideal SOI partner.





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# **Thin-SOI Solutions**

### **Thin-SOI Specification**

Parameter	Specification Range
Wafer Diameter	100 – 200 mm
Handle Layer Specifications	
Dopant Type	N or P
Doping	N type: Phos, Sb & As
	P type: Boron
Resistivity	≤0.001 - ≥10000 Ω-cm
Growth Method	CZ, MCZ or FZ
Buried Oxide Specifications	
Thermally Oxidised Buried Oxide	0.1um – 3µm grown on Device or both wafers
Thickness	
Buried Oxide Uniformity	± 5%
Device Layer Specifications	
Device Layer Thickness	0.1um – 1um
Device Layer Uniformity	± 20nm
Dopant Type	N or P
Doping	N type: Phos, Sb & As
	P type: Boron
Resistivity	≤0.001 - ≥10000 Ω-cm
Growth Method	CZ, MCZ or FZ
Crystal Orientation	<100>, <111> or <110>

The above is a standard IceMOS specification; however, we are always happy to work with our customers to engineer specific solutions. If you would like to discuss an alternative specification, please contact our sales team: sales@icemostech.com